

ENTERPRISE CORP. HITANO ENTERPRISE CORP.

SD820S THRU SD8100S

TECHNICAL SPECIFICATIONS OF SURFACE MOUNT SCHOTTKY BARRIER DIODE VOLTAGE RANGE - 20 to 100 Volts CURRENT - 8.0 Amperes

FEATURES

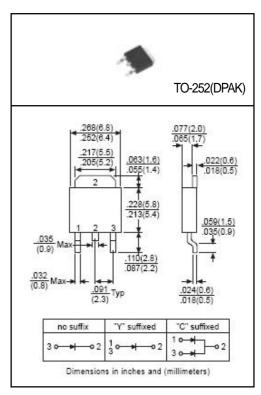
- * Metal to silicon rectifier majority carrier conduction
- * Low power loss, High efficiency
- * High current capability
- * Low forward voltage drop
- * High surge capacity
- * For use in low voltage high frequency inverters, free wheeling, and polarity protection applications

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Terminals: Solder plated, solderable per
 - MIL-STD-750, Method 2026
- * Mounting position: Any* Weight: 0.4 grams Approx.

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25° C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.



		SYMBOL	SD820S	SD830S	SD840S	SD850S	SD860S	SD880S	SD8100S	UNITS
Maximum Recurrent Peak Reverse Voltage		VRRM	20	30	40	50	60	80	100	Volts
Maximum RMS Voltage		VRMS	14	21	28	35	42	56	70	Volts
Maximum DC Blocking Voltage		VDC	20	30	40	50	60	80	100	Volts
Maximum Average Forward Rectified Current at TC=75°C		lo	8.0							Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	100							Amps
Maximum Instantaneous Forward Voltage at 4.0A DC for "C suffixed", and at 8.0A DC for "Y suffixed" & "no suffix"		VF	0.65			0.75 0.		.85	Volts	
Maximum DC Reverse Current at Rated DC Blocking Voltage	@TA = 25°C		2.0							mAmps
	@Ta = 100°C	lr.	50							
Typical Thermal Resistance (Note1)		RθJA	80							°C/W
Typical Junction Capacitance (Note 2)		CJ	700							pF
Storage Operating Temperature Range		TJ, TSTG	-55 to + 125							٥C

Note: 1. Mounted on PC Board with 14mm² (0.013mm thick) copper pad areas.

^{2.} Measured at 1 MHz and applied reverse voltage of 4.0 volts.

RATING AND CHARACTERISTIC CURVES (SD820S THRU SD8100S)

